

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	309	438/162.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/05 08:51
L2	1132	438/166.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/05 09:13
L3	916	438/289.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/05 09:13
L4	175	438/473.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/05 09:14
L5	444	438/528.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/05 09:46
L6	620	438/486.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/05 09:46
L7	536	(silicon or semiconductor or substrate) near5 (ion near bombard\$4 or amorphi\$4) and (implant\$4) near5 (fluorine or f! or carbon or c! or chlorine or cl or nitrogen or n!)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/05 10:12
L8	286	(silicon or semiconductor or substrate) near5 (ion near bombard\$4 or amorphi\$4) and (implant\$4) near5 (fluorine or f! or carbon or c! or chlorine or cl or nitrogen or n!) and (doping or dopant or impurity or boron or b) near4 (diffusion or diffusing or diffused or migration or migrating or migrated)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/05 10:42

EAST Search History

L9	506	(source or drain) near8 (dopant near layer or dopant near coating or (silicate near glass or bpsg or psg or bsg) near2 (doping or dopant or impurity))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/05 10:59
L10	146	(source or drain) near8 (dopant near layer or dopant near coating or (silicate near glass or bpsg or psg or bsg) near2 (doping or dopant or impurity)) and ((implant or implanted or implanting) near3 (fluorine or f or carbon or c or nitrogen or n or chlorine or cl) or ion near bombard\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/05 11:25
L11	86	(doped near dielectric or dopant near coating or (silicate near glass or bpsg or psg or bsg) near2 (doping or dopant or impurity)) near6 (diffus\$4) and ((implant or implanted or implanting) near3 (fluorine or f or carbon or c or nitrogen or n or chlorine or cl) or ion near bombard\$4 or amorphi\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/05 11:34
L12	251	(fsg or bsg or bpsg or psg or glass or silicate) near4 (doping or dopant or doped) near6 (amorphous or amorphizing or alpha or a-Si)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/05 11:41
L14	59	(ultrashallow or ultra-shallow) near2 junction and (fluorine or carbon or fluoride or carbide) near2 (implant\$4 or co-doping or doping or doped or dopant or impurity)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/05 11:47
L15	368	(shallow or ultrashallow or narrow) near4 junction and (carbon or c! or fluorine or f!) near4 (doping or dopant or doped or implanted or implantation or implant or implanting) and (amorphizing or pre-amorphizing or amorphous) and (dopant or boron or b or phosphorus or p or arsenic or as or transient) near2 (diffusion or diffusing or diffused or spread or spreading)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/05 11:52
L16	239	(carbon or fluorine) near4 (boron) near4 (diffusion or ted or diffusivity)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/05 12:25

EAST Search History

L17	1787	(438/162,166,289,473,486,528.ccls. or 257/E21.133.ccls.) and (amorphization or pre-amorphization or (implant\$5 or bombard\$5) near5 (Ge or germanium or si or silicon or sb or antimony or in or indium or ar or argon))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/05 12:27
L18	484	(438/162,166,289,473,486,528.ccls. or 257/E21.133.ccls.) and (amorphization or pre-amorphization or (implant\$5 or bombard\$5) near5 (Ge or germanium or si or silicon or sb or antimony or in or indium or ar or argon)) and (fluorine or f! or carbon or c!) near4 (doping or doped or dopant or implant or implantation or implanted or implanting)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/05 12:52
L19	76	(438/162,166,289,473,486,528.ccls. or 257/E21.133.ccls.) and (transient near enhanced near diffusion or ted)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/05 12:46
L20	139	(438/162,166,289,473,486,528.ccls. or 257/E21.133.ccls.) and (amorphization or pre-amorphization or amorphous) near10 ((implant\$5 or bombard\$5) near5 (Ge or germanium or si or silicon or sb or antimony or in or indium or ar or argon)) and (fluorine or f! or carbon or c!) near4 (doping or doped or dopant or implant or implantation or implanted or implanting) and (boron or b!) near8 (doping or doped or diffusion or diffusivity or diffusing or implant\$5)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/05 13:15
L21	91	(amorphization or pre-amorphization or amorphous) near7 (carbon or fluorine or c or f) near6 (doping or dopant or doped or implant\$5) near10 (anneal\$5 or recrystal\$7 or crystal\$7) and (boron or B) near6 (doping or doped or dopant or impurity or implant\$5)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/05 13:31
L22	384	(shallow or ultrashallow) near2 (junction) and (diffusivity or diffusion or ted) near4 (boron or dopant or impurity) and (carbon or fluorine or c or f) near3 (doping or doped or dopant or implant\$5)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/05 13:35

EAST Search History

L23	305	(shallow or ultrashallow) near2 (junction) and (diffusivity or diffusion or ted) near4 (boron or dopant or impurity) and (carbon or fluorine or c or f) near3 (doping or doped or dopant or implant\$5) and (pre-amorphiz\$7 or preamorphiz\$7 or amorphiz\$6 or (implant\$6 or bombard\$6) near4 (silicon or si or germanium or ge or argon or ar or indium or in or antimony or sb))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/05 13:47
L24	137	(shallow or ultrashallow) near2 (junction) and (diffusivity or diffusion or ted) near4 (boron or dopant or impurity) and (carbon or fluorine or c or f) near3 (doping or doped or dopant or implant\$5) same (pre-amorphiz\$7 or preamorphiz\$7 or amorphiz\$6 or (implant\$6 or bombard\$6) near4 (silicon or si or germanium or ge or argon or ar or indium or in or antimony or sb))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/05 13:48

Interference Search

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L25	26	(pre-amorphiz\$6 or preamorphiz\$6).clm.	US-PGPUB	OR	OFF	2006/06/05 13:55
L26	6	((shallow near2 junction or ultrashallow near junction or transient near enhanced near diffusion or ted or boron near diffusi\$4) near15 (carbon or c or fluorine or f) near4 (doping or doped or dopant or implant\$5)).clm.	US-PGPUB	OR	OFF	2006/06/05 13:54
L27	5	((pre-amorphiz\$6 or preamorphiz\$6 or (implant\$5 or bombard\$5) near2 (silicon or si or germanium or ge or argon or ar or indium or in or antimony or sb)) and (fluorine or carbon or f or c) near4 (doping or doped or implant\$5)).clm.	US-PGPUB	OR	OFF	2006/06/05 13:57
L29	1	((transistor or mosfet or pmos or nmos) and (pre-amorphiz\$5 or amorphiz\$5 or (implant\$5 or bombard\$5) near2 (si or silicon or ge or germanium or ar or argon or in or indium or sb or antimony)) and (boron or dopant or impurity) near3 (diffusivity or ted or transient near enhanced near diffusion)).clm.	US-PGPUB	OR	OFF	2006/06/05 14:00
L30	72	((transistor or mosfet or pmos or nmos) and (pre-amorphiz\$5 or amorphiz\$5 or (implant\$5 or bombard\$5) near2 (si or silicon or ge or germanium or ar or argon or in or indium or sb or antimony)) same (boron or dopant or impurity) near4 (diffus\$6 or target or implant\$5)).clm.	US-PGPUB	OR	OFF	2006/06/05 14:00